

# HMC322LP4 / 322LP4E

v06.0112



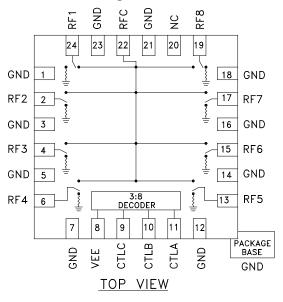
## GaAs MMIC SP8T NON-REFLECTIVE SWITCH. DC - 8 GHz

### Typical Applications

This switch is suitable for usage in DC - 8.0 GHz 50-Ohm or 75-Ohm systems:

- Broadband
- Fiber Optics
- Switched Filter Banks
- Wireless below 8 GHz

## **Functional Diagram**



#### **Features**

Broadband Performance: DC - 8.0 GHz

High Isolation: >30 dB@ 6 GHz Low Insertion Loss: 2.4 dB@ 6 GHz

Integrated 3:8 TTL Decoder

24 Lead 4x4mm QFN Package: 9 mm<sup>2</sup>

### **General Description**

The HMC322LP4 & HMC322LP4E are broadband non-reflective GaAs MESFET SP8T switches in low cost leadless surface mount packages. Covering DC to 8 GHz, this switch offers high isolation and low insertion loss. This switch also includes an on board binary decoder circuit which reduces the required logic control lines to three. The switch operates using a negative control voltage of 0/-5 volts, and requires a fixed bias of -5V. This switch is suitable for usage in 50-Ohm or 75-Ohm systems.

## Electrical Specifications, $T_A = +25^{\circ}$ C, With 0/-5V Control, 50 Ohm System

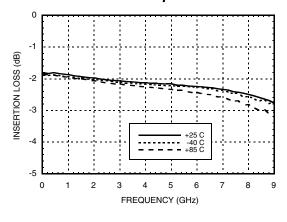
Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 2.0 GHz DC - 4.0 GHz DC - 8.0 GHz		2.1 2.3 2.5	2.5 2.7 2.9	dB dB dB
Isolation		DC - 2.0 GHz DC - 4.0 GHz DC - 6.0 GHz DC - 8.0 GHz	35 30 25 20	40 35 30 25		dB dB dB dB
Return Loss	"On State"	DC - 2.0 GHz DC - 8.0 GHz	9 6	12 10		dB dB
Return Loss	"Off State"	DC - 8.0 GHz	7	10		dB
Input Power for 1 dB Compression		0.5 - 8.0 GHz	19	23		dBm
Input Third Order Intercept (Two-Tone Input Power = +7 dBm Each Tone)		0.5 - 8.0 GHz	36	40		dBm
Switching Characteristics tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)		DC - 8.0 GHz		50 150		ns ns



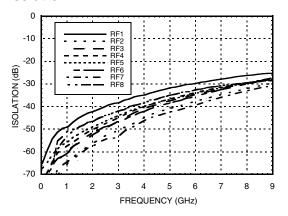


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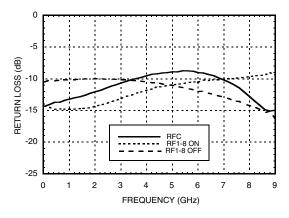
### Insertion Loss vs. Temperature



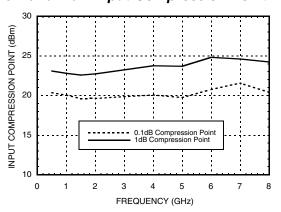
#### Isolation



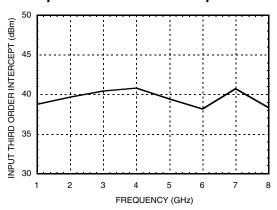
#### **Return Loss**



### 0.1 and 1 dB Input Compression Point



### **Input Third Order Intercept Point**







## GaAs MMIC SP8T NON-REFLECTIVE SWITCH, DC - 8 GHz

### Bias Voltage & Current

Vee Range = -5.0 Vdc ± 10%			
Vee (Vdc)	lee (Typ.) (mA)	lee (Max.) (mA)	
-5.0	5.0	9.0	

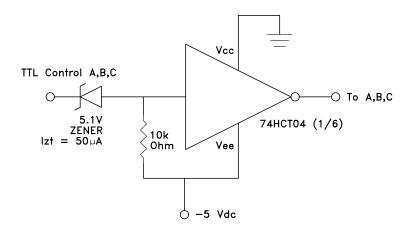
### **Control Voltages**

State	Bias Condition
Low	-3V to 0 Vdc @ 25 μA Typical
High	-5 to -4.2 Vdc @ 5 μA Typical

#### **Truth Table**

Control Input		t	Signal Path State
Α	В	С	RFCOM to:
High	High	High	RF1
Low	High	High	RF2
High	Low	High	RF3
Low	Low	High	RF4
High	High	Low	RF5
Low	High	Low	RF6
High	Low	Low	RF7
Low	Low	Low	RF8

### **TTL Interface Circuit**



#### Note:

Control inputs A, B, and C can be driven directly with TTL logic with -5 Volts applied to the HCT logic gates Vee pin and to Vee (pin 8) of the RF Switch.





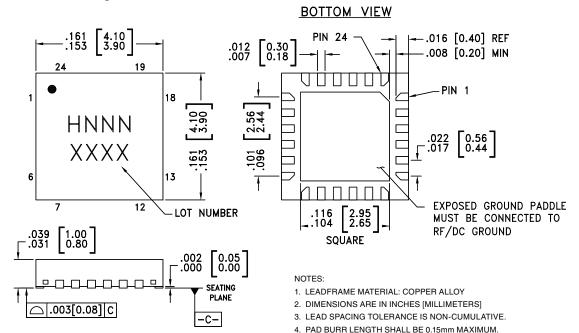
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### **Absolute Maximum Ratings**

Bias Voltage Range (Vee)	-7.0 Vdc
Control Voltage Range (A, B, & C)	Vee -0.5V to +1.0 Vdc
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
Maximum Input Power	26 dBm
Channel Temperature	150 ° C
Continuous Pdiss ( T = 85 ° C ) ( derate 5.34 mW / ° C )	0.348 W
Thermal Resistance	187 ° C / W
ESD Sensitivity (HBM)	Class 1B



## **Outline Drawing**



## Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC322LP4	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H322 XXXX
HMC322LP4E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H322 XXXX

PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
6. ALL GROUND LEADS AND GROUND PADDLE MUST BE

7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED

SOLDERED TO PCB RF GROUND.

LAND PATTERN.

- [1] Max peak reflow temperature of 235  $^{\circ}\text{C}$
- [2] Max peak reflow temperature of 260  $^{\circ}\text{C}$
- [3] 4-Digit lot number XXXX





## GaAs MMIC SP8T NON-REFLECTIVE SWITCH, DC - 8 GHz

### **Pin Descriptions**

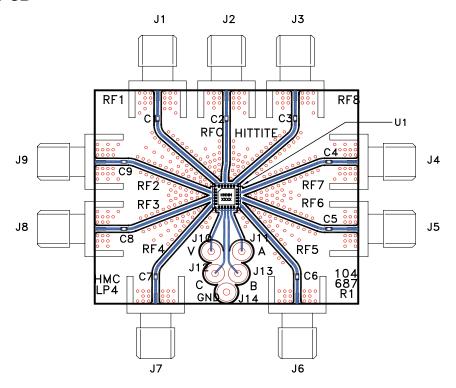
Pin Number	Function	Description	Interface Schematic
1, 3, 5, 7, 12, 14, 16, 18, 21, 23	GND	Package bottom has exposed metal paddle that must also be connected to PCB RF ground.	Ģ GND =
2, 4, 6, 13, 15, 17, 19, 22, 24	RF1 - RF8 & RFC	This pin is DC coupled and matched to 50 Ohm. Blocking capacitors are required if RF line potential is not equal to 0V.	
8	VEE	Supply Voltage = -5V ± 10%	VEE 05pF
9	CTLC	See truth table and control voltage table.	<u></u>
10	CTLB	See truth table and control voltage table.	200K
11	CTLA	See truth table and control voltage table.	VEE
20	N/C	This pin should be connected to PCB RF ground to maximize isolation.	





## GaAs MMIC SP8T NON-REFLECTIVE SWITCH, DC - 8 GHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 107780 [1]

Item	Description
J1 - J9	PCB Mount SMA RF Connector
J10 - J14	DC Pin
C1 - C9	100 pF Capacitor, 0402 Pkg.
U1	HMC322LP4 / HMC322LP4E SP8T Switch
PCB [2]	104687 Evaluation PCB 1.73"x1.46"

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads and backside ground slug should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.